

# **HAT2189WP**

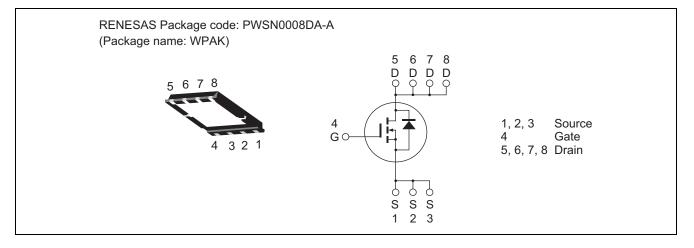
# Silicon N Channel Power MOS FET Power Switching

REJ03G1251-0200 Rev.2.00 Aug 28, 2009

# Features

- Low on-resistance
- Low drive current
- High density mounting

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	200	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	8.5	А
Drain peak current	Note1 I <sub>D (pulse)</sub>	17	А
Body-drain diode reverse drain current	I <sub>DR</sub>	8.5	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	17	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	8.5	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	4.8	mJ
Channel dissipation	Pch Note2	20	W
Channel to case thermal impedance	θch-c	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

3. STch = 25°C, Tch  $\leq$  150°C



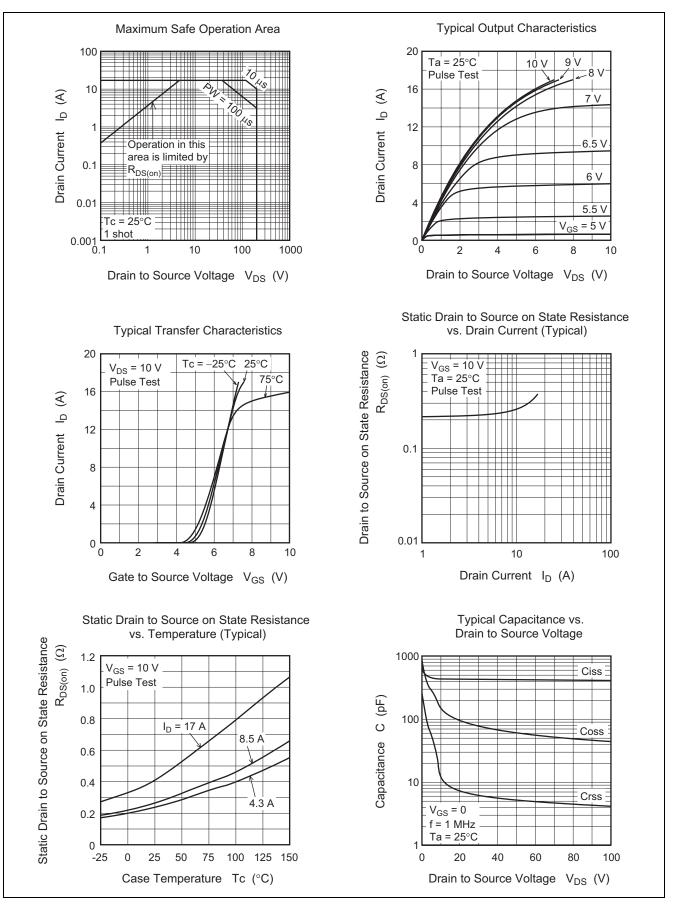
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	200	—	_	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS}$ = 200 V, $V_{GS}$ = 0
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μA	$V_{GS}$ = ±30 V, $V_{DS}$ = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	_	4.5	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA
Forward transfer admittance	y <sub>fs</sub>	3.5	6.0	_	S	$I_D$ = 4.3 A, $V_{DS}$ = 10 V <sup>Note4</sup>
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	0.23	0.27	Ω	$I_D$ = 4.3 A, $V_{GS}$ = 10 V <sup>Note4</sup>
Input capacitance	Ciss		430	_	pF	V <sub>DS</sub> = 25 V V <sub>GS</sub> = 0 f = 1 MHz
Output capacitance	Coss		86	_	pF	
Reverse transfer capacitance	Crss	_	7	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	24	_	ns	I <sub>D</sub> = 4.3 A
Rise time	tr	_	24	—	ns	$V_{GS}$ = 10 V R <sub>L</sub> = 23.3 Ω Rg = 10 Ω
Turn-off delay time	t <sub>d(off)</sub>	_	44	—	ns	
Fall time	t <sub>f</sub>	_	9	—	ns	
Total gate charge	Qg	_	10	—	nC	V <sub>DD</sub> = 160 V V <sub>GS</sub> = 10 V I <sub>D</sub> = 8.5 A
Gate to source charge	Qgs	_	2.7	_	nC	
Gate to drain charge	Qgd	_	3.8	_	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.9	1.4	V	$I_F = 8.5 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	100	_	ns	$I_F$ = 8.5 A, $V_{GS}$ = 0 di <sub>F</sub> /dt = 100 A/µs

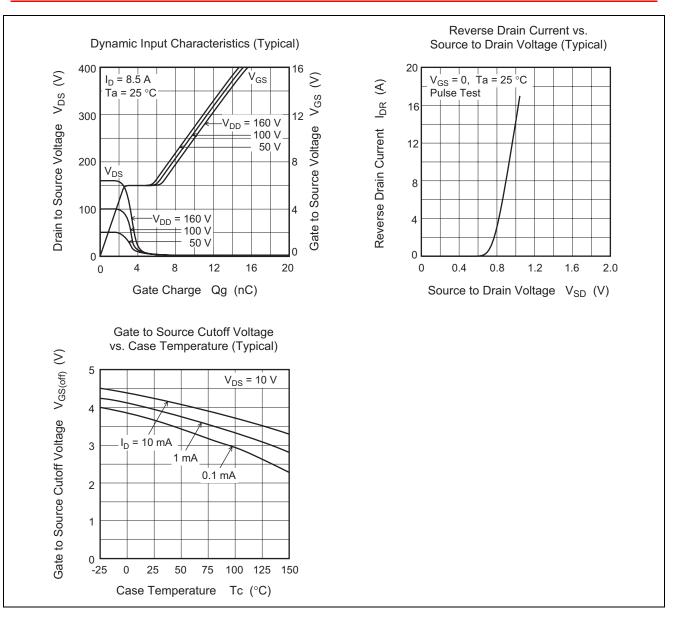
Notes: 4. Pulse test



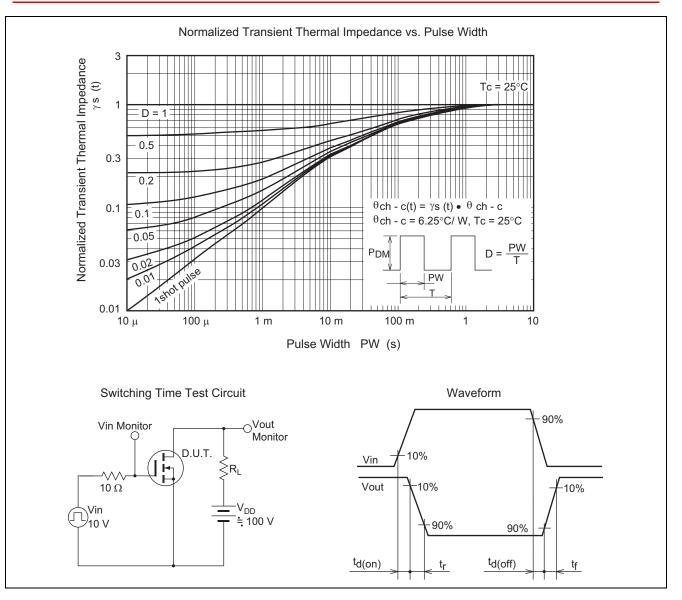
## **Main Characteristics**



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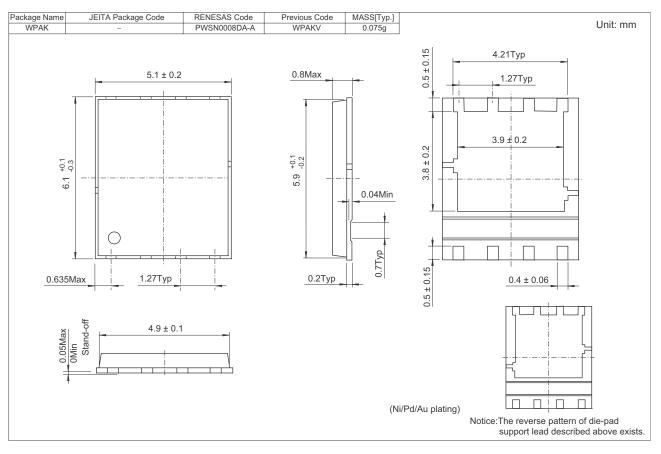


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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2189WP-EL-E	2500 pcs	Taping



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